

Anhang A: Verwendete Schichtstruktur

Kontaktschicht	50 nm	InGaAsP:Zn $p = 5 \times 10^{18} \text{ cm}^{-3}$		
Oberer Mantel	300 nm	InP:Zn $p = 1 \times 10^{18} \text{ cm}^{-3}$	p	
	300 nm	InP:Zn $p = 4 \times 10^{17} \text{ cm}^{-3}$		
Kern	14 x	100 nm	InGaAsP nid	i
		8 nm	InGaAsP nid $\lambda = 1,15 \mu\text{m}$ $\varepsilon = +0,2 \%$	
		5,5 nm	InGaAs nid $\varepsilon = -0,3 \%$	
		32 nm	InGaAsP nid $\lambda = 1,15 \mu\text{m}$	
		100 nm	InGaAsP nid $\lambda = 1,33 \mu\text{m}$	
Unterer Mantel	300 nm	InP:Si $p = 5 \times 10^{17} \text{ cm}^{-3}$	n	
	300 nm	InP:Si $p = 1 \times 10^{18} \text{ cm}^{-3}$		
Ätzstoppschicht	50 nm	InGaAsP nid $\lambda = 1,33 \mu\text{m}$	i	
Substrat		InP:Fe		